

2826

**STATEMENT UNDER 37 CFR 1.97(e) ACCOMPANYING
INFORMATION DISCLOSURE STATEMENT**

Docket No.
BUR920000059US1

In Re Application Of: **Bryant et al.**

MAR 31 2003

#7

Serial No.
09/886,823

Filing Date
06/21/01

Examiner
Abraham, F.

Group Art Unit
2826

Invention: **DOUBLE GATED TRANSISTOR AND METHOD OF FABRICATION**

TO THE ASSISTANT COMMISSIONER FOR PATENTS:

This is a statement under the provisions of 37 CFR 1.97(e) in the above-identified application.

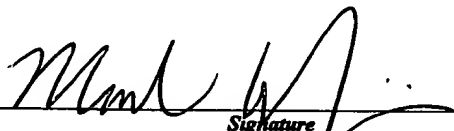
Check applicable statement herebelow:

Statement Under 37 CFR 1.97(e)(1)

- ☒ Each item of information contained in the accompanying Information Disclosure Statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the Information Disclosure Statement.

Statement Under 37 CFR 1.97(e)(2)

- ☐ No item of information contained in the accompanying Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application, and, to the knowledge of the undersigned person, after making reasonable inquiry, no item of information contained in the accompanying Information Disclosure Statement was known to any individual designated in 37 CFR 1.56(c) more than three months prior to the filing of the Information Disclosure Statement.


Signature

Dated: **26 March 2003**

**Mark F. Chadurjian
Registration No. 30,739
International Business Machines Corporation
Intellectual Property Law - Mail 972E
1000 River Street
Essex Junction, VT 05452**

Phone: (802) 769-8843

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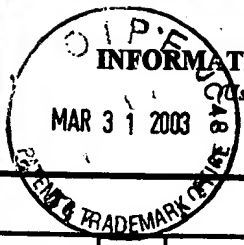


Signature of Person Mailing Correspondence

Pat Blair

Typed or Printed Name of Person Mailing Correspondence

CC:



INFORMATION DISCLOSURE CITATION

(Use several sheets if necessary)

Docket Number (Optional)

BUR920000059US1

Application Number

09/886,823

Applicant(s)

Bryant et al.

Filing Date

06/21/01

Group Art Unit

2826

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
		5,899,710	05/04/99	Mukai	438	156	
		6,197,672	03/06/01	Lin et al.	438	592	

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
		EP 0 694 977 A2	01/31/96	European (DE, FR, GB, NL)				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

		Kim K et al., "Double-Gate CMOS: Symmetrical-Versus Asymmetrical-Gate Devices", IEEE Transactions on Electron Devices, IEEE Inc. New York, US, vol. 48, no. 2, February 2001 (2001-02), pages 294-299, XP001038978, ISSN: 0018-9383

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.